PLASMA PROCESSING APPARATUS

Abstract

In a plasma processing apparatus, an influence on plasma processing of a substrate due to the wear of components in a chamber is reduced. The plasma processing apparatus includes a chamber; a substrate support; an edge ring; an upper electrode; a first gas supply; an RF power source; a DC power source configured to apply a DC voltage to the edge ring; a first counter configured to count a first time according to an operation time of the RF power source and to reset the first time by replacing the upper electrode; a second counter configured to count a second time according to the operation time of the RF power source and to reset the second time by replacing the edge ring; a first processor configured to stepwisely change at least one of the RF power and the first gas according to the first time; and a second processor configured to stepwisely change the DC voltage according to the second time.

Fig. 2